Fast Switching Diode

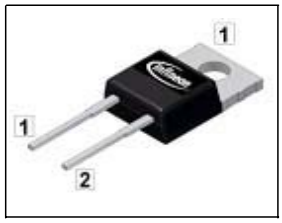
Features

- 1200 V diode technology
- Fast recovery
- Soft switching
- Low reverse recovery charge
- Low forward voltage
- Easy paralleling
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Qualified according to JEDEC for target applications

Product Summary

V_{RRM}	1200	V
I_F	30	A
V_F	1.65	V
T_{jmax}	150	°C

PG-TO220-2



Type	Package	Ordering Code	Marking	Pin 1	PIN 2	PIN 3
IDP30E120	PG-TO220-2	-	D30E120	C	A	-

Maximum Ratings, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	1200	V
Continous forward current	I_F		A
T_C=25°C		50	
T_C=90°C		30	
Surge non repetitive forward current T_C=25°C, t_p=10 ms, sine halfwave	I_{FSM}	102	
Maximum repetitive forward current T_C=25°C, t_p limited by T_{jmax}, D=0.5	I_{FRM}	76.5	
Power dissipation	P_{tot}		W
T_C=25°C		138	
T_C=90°C		66	
Operating and storage temperature	T_j , T_{stg}	-55...+150	°C
Soldering temperature wavesoldering, 1.6mm (0.063 in.) from case for 10s	T_S	260	°C

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	0.9	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	-	62	
@ 6 cm^2 cooling area [1)]		-	35	-	

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Reverse leakage current	I_R				µA
V_R=1200V, T_j=25°C		-	-	100	
V_R=1200V, T_j=150°C		-	-	2500	
Forward voltage drop	V_F				V
I_F=30A, T_j=25°C		-	1.65	2.15	
I_F=30A, T_j=150°C		-	1.7	-	

[0]J-STD20 and JESD22

[1]Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical without blown air.

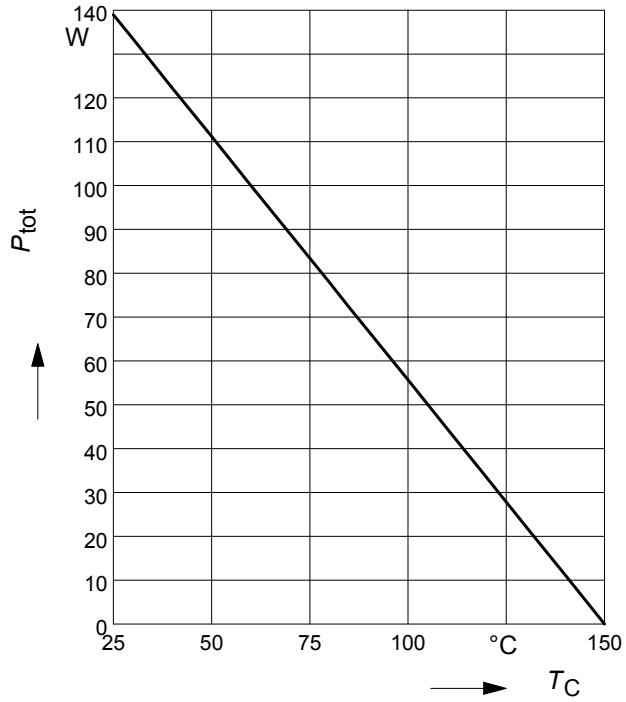
Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Reverse recovery time	t_{rr}				ns
V_R=800V, I_F=30A, di_F/dt=850A/µs, T_j=25°C		-	243	-	
V_R=800V, I_F=30A, di_F/dt=850A/µs, T_j=125°C		-	355	-	
V_R=800V, I_F=30A, di_F/dt=850A/µs, T_j=150°C		-	380	-	
Peak reverse current	I_{rrm}				A
V_R=800V, I_F = 30 A, di_F/dt=850A/µs, T_j=25°C		-	23.7	-	
V_R=800V, I_F =30A, di_F/dt=850A/µs, T_j=125°C		-	28.3	-	
V_R=800V, I_F =30A, di_F/dt=850A/µs, T_j=150°C		-	29.5	-	
Reverse recovery charge	Q_{rr}				nC
V_R=800V, I_F=30A, di_F/dt=850A/µs, T_j=25°C		-	2630	-	
V_R=800V, I_F =30A, di_F/dt=850A/µs, T_j=125°C		-	4700	-	
V_R=800V, I_F =30A, di_F/dt=850A/µs, T_j=150°C		-	5200	-	
Reverse recovery softness factor	S				
V_R=800V, I_F=30A, di_F/dt=850A/µs, T_j=25°C		-	6	-	
V_R=800V, I_F=30A, di_F/dt=850A/µs, T_j=125°C		-	7.4	-	
V_R=800V, I_F=30A, di_F/dt=850A/µs, T_j=150°C		-	7.5	-	

1 Power dissipation

$P_{tot} = f(T_C)$

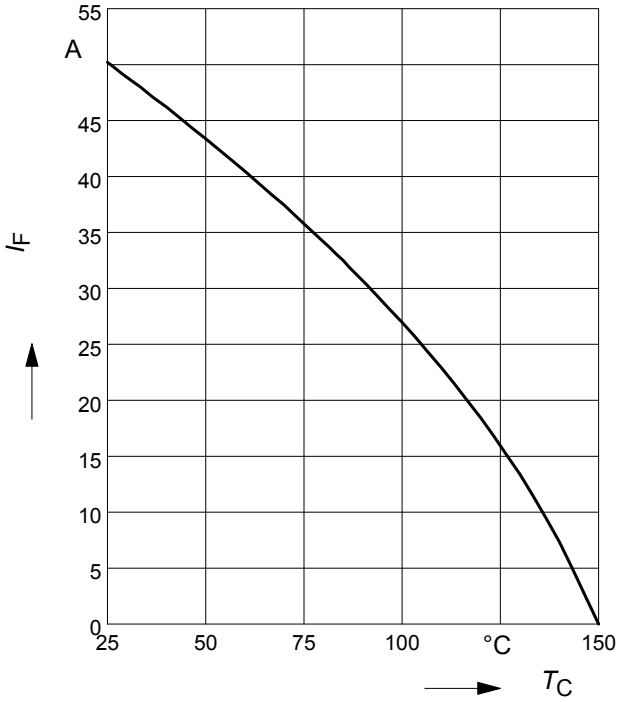
parameter: $T_j \leq 150°C$



2 Diode forward current

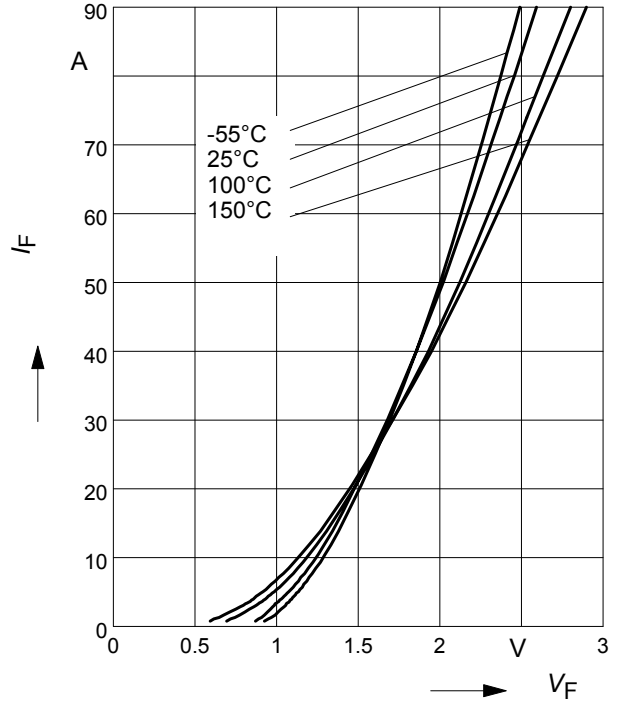
$I_F = f(T_C)$

parameter: $T_j \leq 150°C$



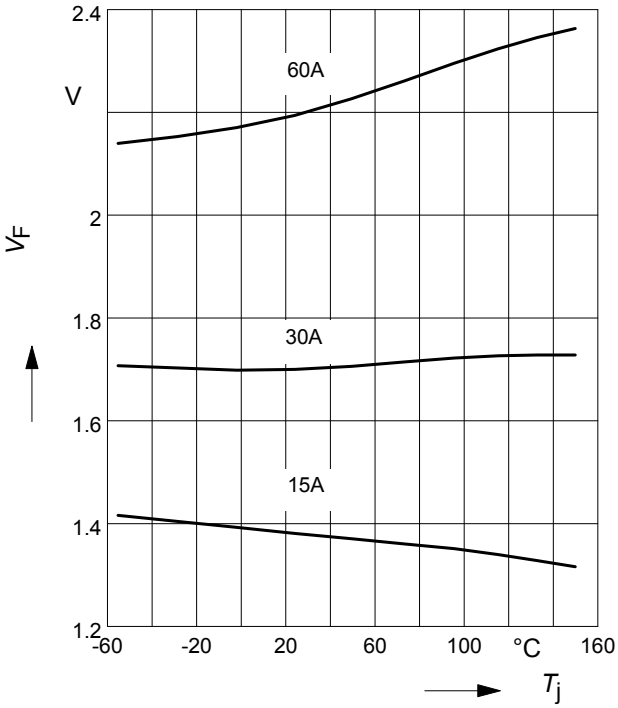
3 Typ. diode forward current

$I_F = f(V_F)$



4 Typ. diode forward voltage

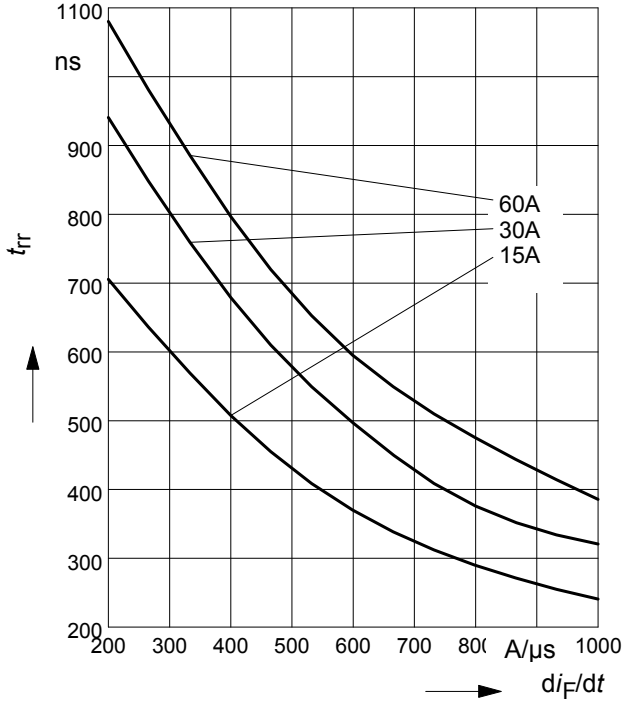
$V_F = f(T_j)$



5 Typ. reverse recovery time

$t_{rr} = f\,(di_F/dt)$

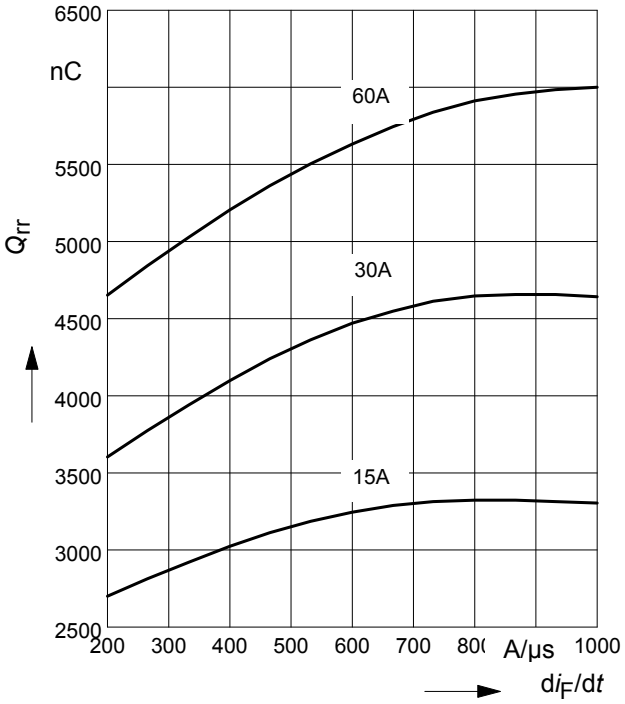
parameter: V_R = 800V, T_j = 125°C



6 Typ. reverse recovery charge

$Q_{rr}=f(di_F/dt)$

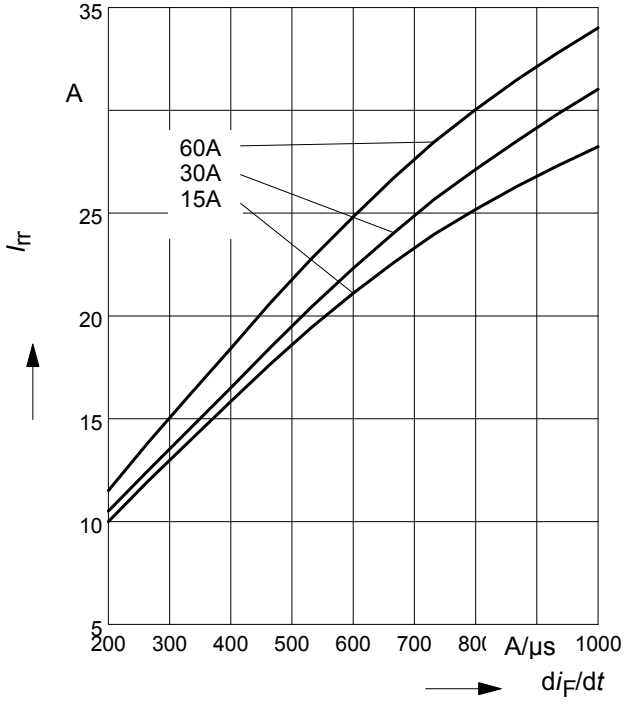
parameter: V_R = 800V, T_j = 125 °C



7 Typ. reverse recovery current

$I_{rr} = f\,(di_F/dt)$

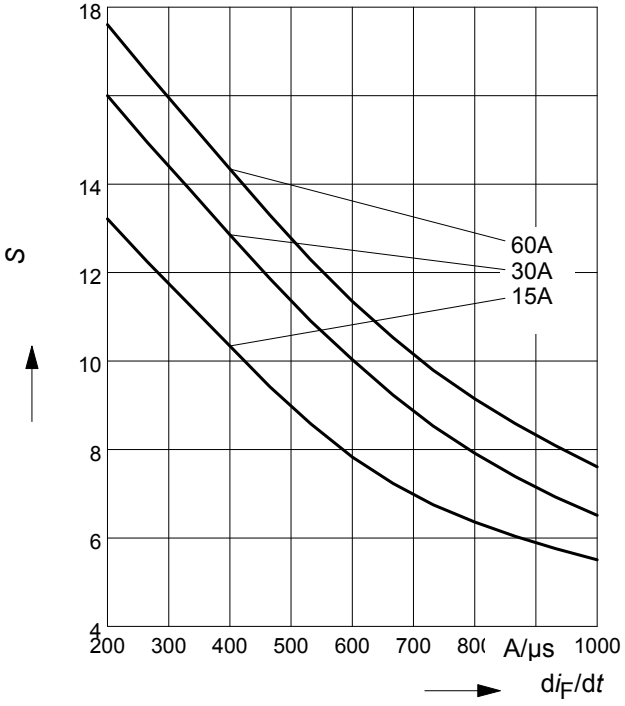
parameter: V_R = 800V, T_j = 125°C



8 Typ. reverse recovery softness factor

S = f(di_F/dt)

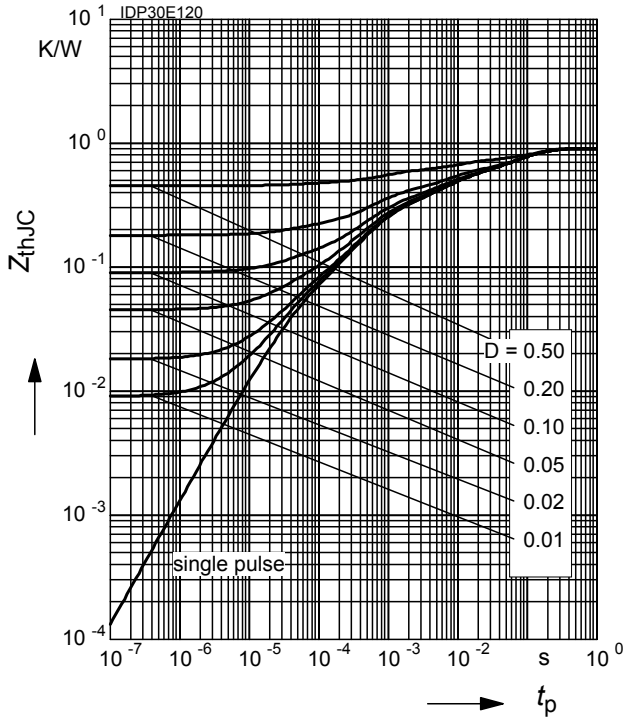
parameter: V_R = 800V, T_j = 125°C



9 Max. transient thermal impedance

$Z_{thJC} = f(t_p)$

parameter : $D = t_p/T$



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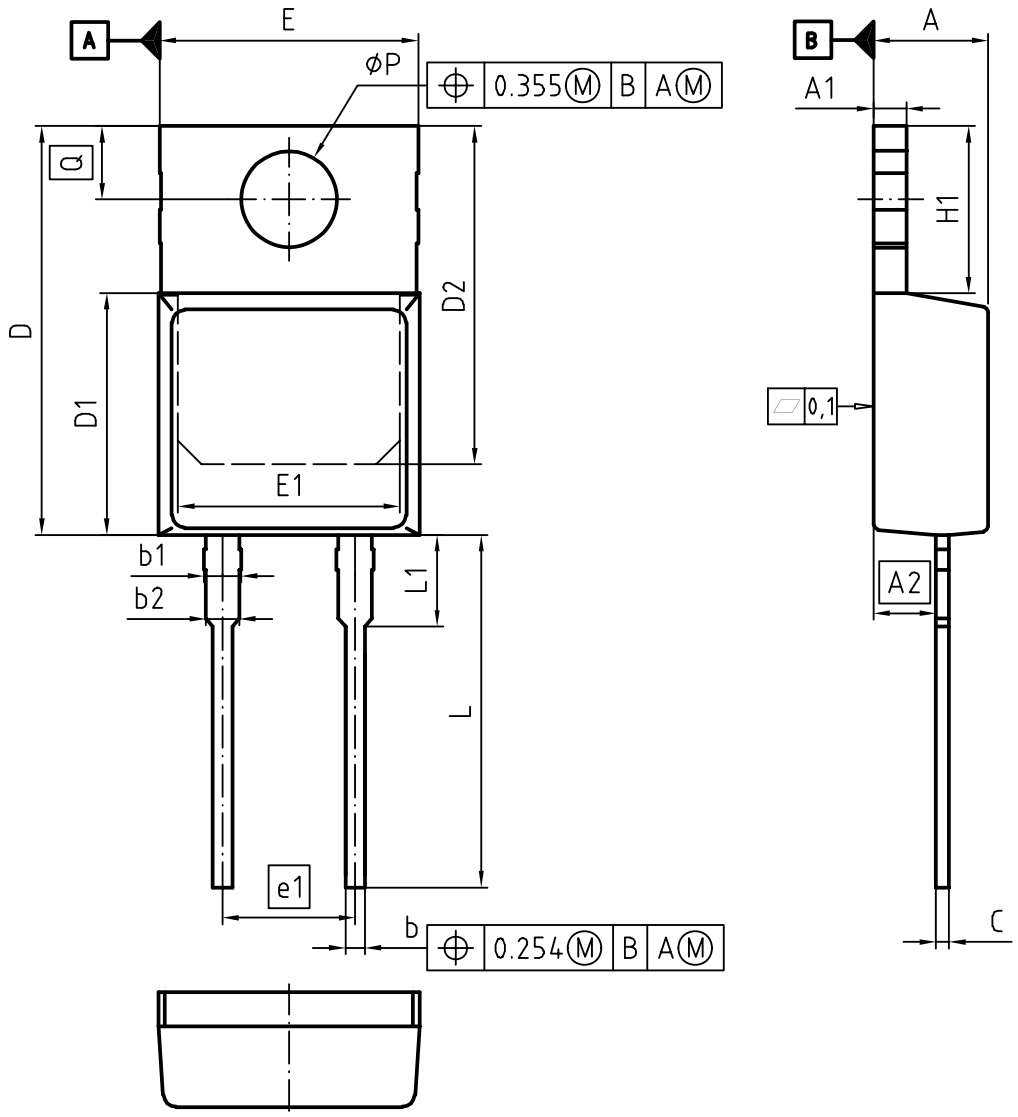

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.50	0.169	0.177
A1	1.17	1.37	0.046	0.054
A2	2.30	2.50	0.091	0.098
b	0.65	0.85	0.026	0.033
b1	1.19	1.69	0.047	0.066
b2	1.19	1.39	0.047	0.055
c	0.40	0.60	0.016	0.024
D	15.35	15.95	0.604	0.628
D1	9.05	9.45	0.356	0.372
D2	12.30	13.05	0.484	0.514
E	9.80	10.20	0.386	0.402
E1	7.25	8.60	0.285	0.339
e1	5.08		0.200	
N	2		2	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	3.30	3.70	0.130	0.146
øP	3.55	3.70	0.140	0.146
Q	2.60	3.00	0.102	0.118

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SCALE 0 2.5 0 2.5 5mm

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